

Description

The SX8P04MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -40V$ $I_D = -8A$

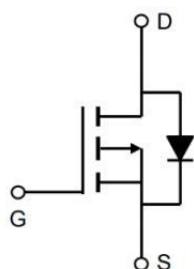
$R_{DS(ON)} < 45m\Omega$ @ $V_{GS} = -10V$

Application

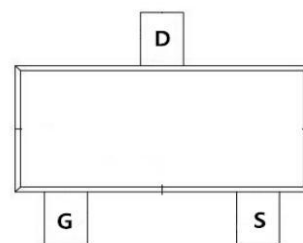
Battery protection

Load switch

Uninterruptible power supply



SOT23-3L



Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-40	V
VGS	Gate-Source Voltage	± 20	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $-V_{GS}$ @ -10V ¹	-8	A
$I_D @ T_c = 100^\circ C$	Continuous Drain Current, $-V_{GS}$ @ -10V ¹	-5.2	A
IDM	Pulsed Drain Current ²	-18	A
EAS	Single Pulse Avalanche Energy ³	37	mJ
$P_D @ T_c = 25^\circ C$	Total Power Dissipation ⁴	31.3	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ C$
TJ	Operating Junction Temperature Range	-55 to 150	$^\circ C$
R θ JA	Thermal Resistance Junction-Ambient ¹	125	$^\circ C/W$
R θ JC	Thermal Resistance Junction-Case ¹	40	$^\circ C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-40	-46	---	V
ΔBVDSS/ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA	---	-0.012	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-18A	---	35	48	mΩ
		V _{GS} =-4.5V , I _D =-12A	---	48	65	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	-1.6	-2.5	V
ΔVGS(th)	VGS(th) Temperature Coefficient		---	4.32	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =-32V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =-32V , V _{GS} =0V , T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-18A	---	12.6	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	13	---	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-20V , V _{GS} =-4.5V , I _D =-12A	---	9	---	nC
Q _{gs}	Gate-Source Charge		---	2.54	---	
Q _{gd}	Gate-Drain Charge		---	3.1	---	
Td(on)	Turn-On Delay Time	V _{DD} =-15V , V _{GS} =-10V , R _G =3.3Ω, I _D =-1A	---	19.2	---	ns
T _r	Rise Time		---	12.8	---	
Td(off)	Turn-Off Delay Time		---	48.6	---	
T _f	Fall Time		---	4.6	---	
Ciss	Input Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz	---	1004	---	pF
Coss	Output Capacitance		---	108	---	
Crss	Reverse Transfer Capacitance		---	80	---	
IS	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	-23	A
ISM	Pulsed Source Current ^{2,5}		---	---	-46	A
VSD	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C	---	---	-1	V

Note :

- 1、 The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 4、 The power dissipation is limited by 150°C junction temperature
- 5、 The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

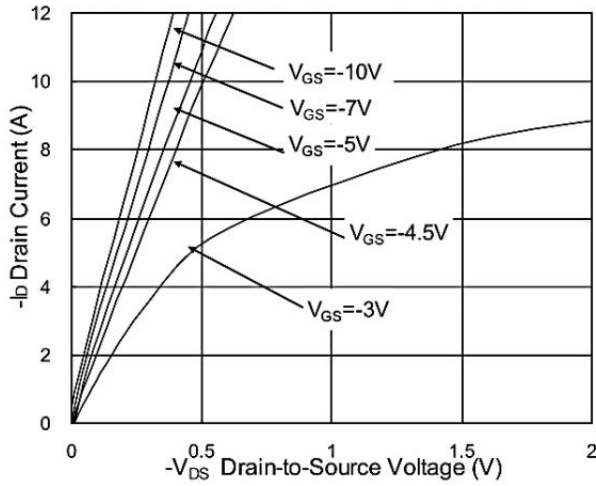


Fig.1 Typical Output Characteristics

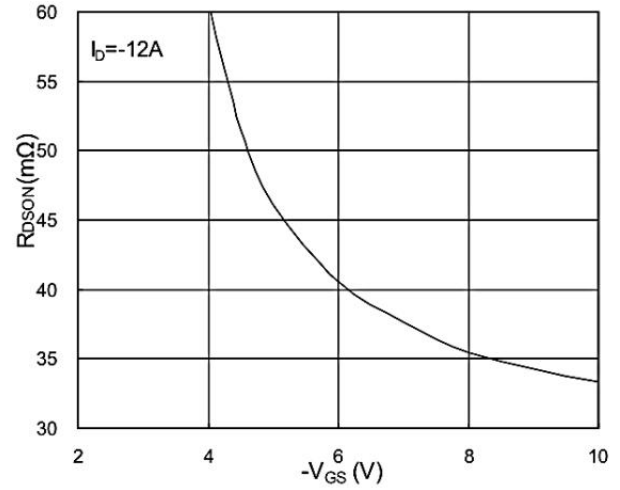


Fig.2 On-Resistance v.s Gate-Source

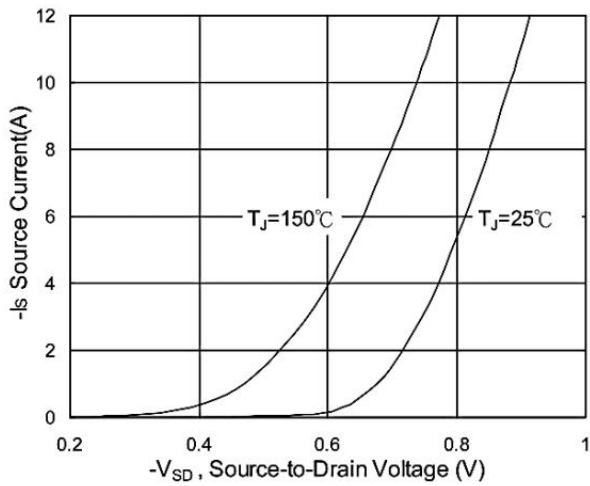


Fig.3 Forward Characteristics of Reverse

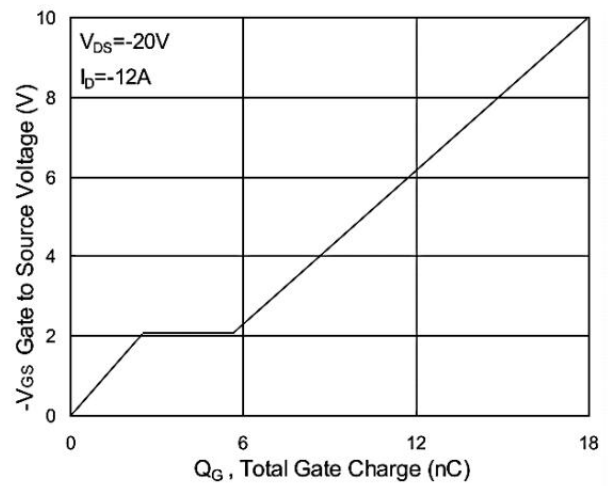


Fig.4 Gate-Charge Characteristics

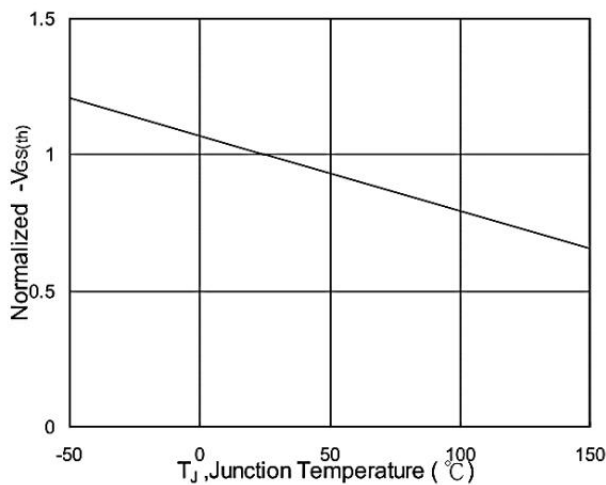


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

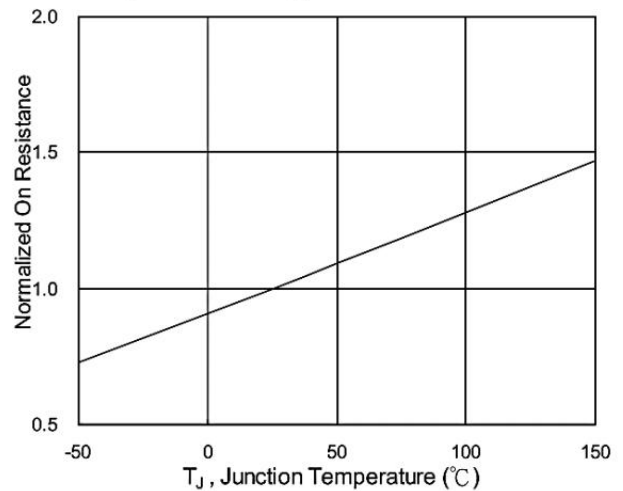


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

Typical Characteristics

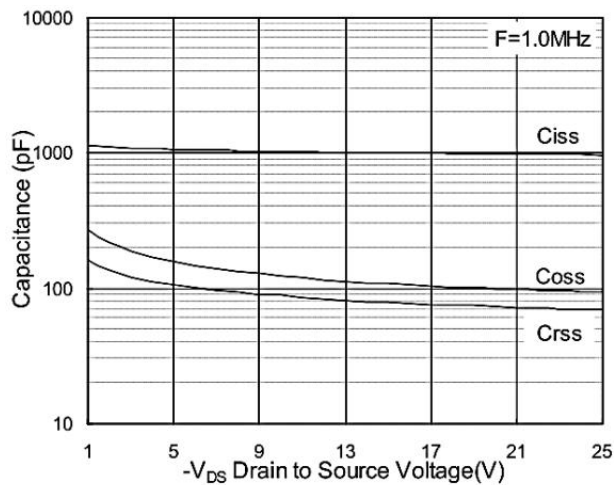


Fig.7 Capacitance

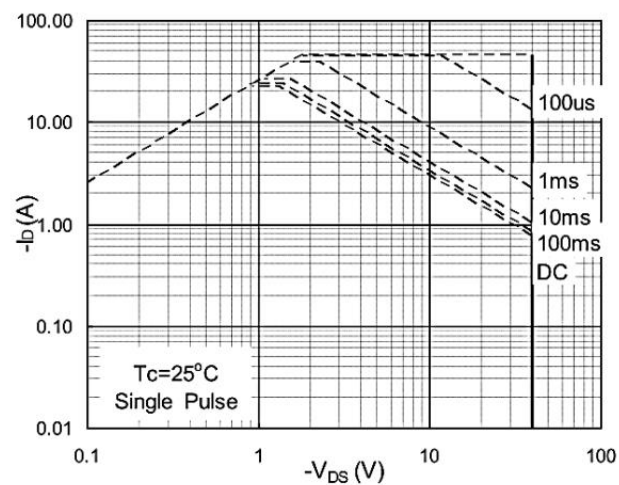


Fig.8 Safe Operating Area

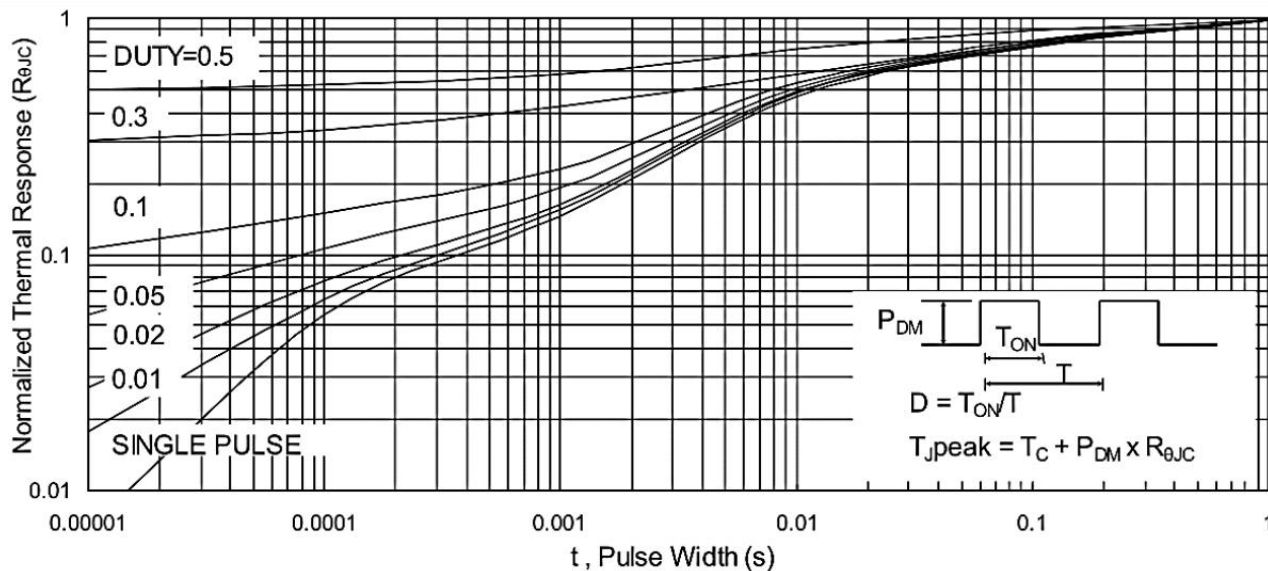


Fig.9 Normalized Maximum Transient Thermal Impedance

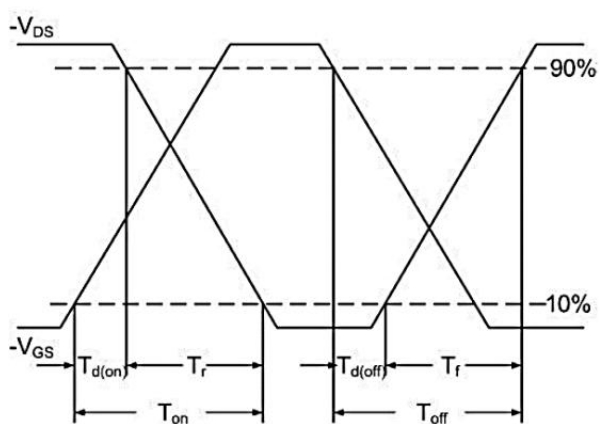


Fig.10 Switching Time Waveform

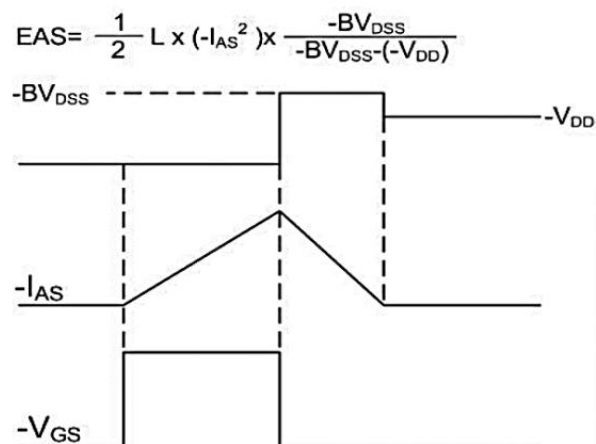
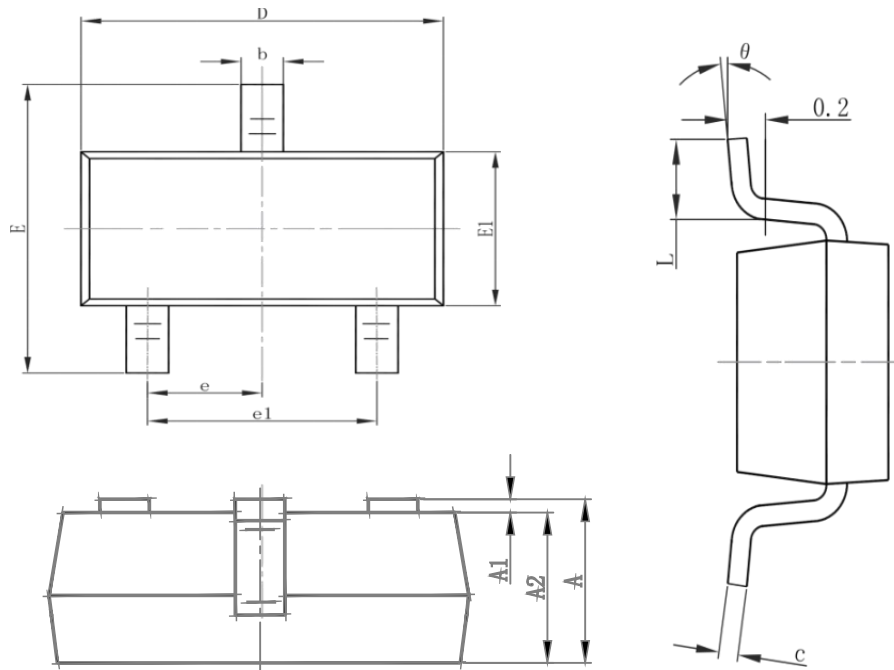


Fig.11 Unclamped Inductive Waveform

Package Mechanical Data-SOT23-3-SLS-Single



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT23-3L		3000